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HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MBR30H100C

General Description

High voltage dual Schottky rectifier suited for switch mode power supplies and other power converters. This device is intended for use in medium voltage operation, and particularly, in high frequency circuits where low switching losses and low noise are required.

MBR30H100C is available in TO-220-3, TO-220-3 (2) and TO-220F-3 packages.

Features

- Low Forward Voltage: 0.67V @ 125°C
- High Surge Capacity
- 175°C Operating Junction Temperature
- 30A Total (15A Each Diode Leg)
- Guard-ring for Stress Protection
- Pb-free Package

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Main Product Characteristics

$I_F (AV)$	2×15A
V_{RRM}	100V
T_J	175°C
$V_F (max)$	0.67V

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets UL 94V-0 @ 0.125in.
- Weight (Approximately):
2Grams (TO-220-3, TO-220-3 (2) and TO-220F-3)
- Finish: All External Surfaces Corrosion Resistant and Terminal
- Leads are Readily Solderable
- Lead Temperature for Soldering Purposes:
260°C Maximum for 10 Seconds

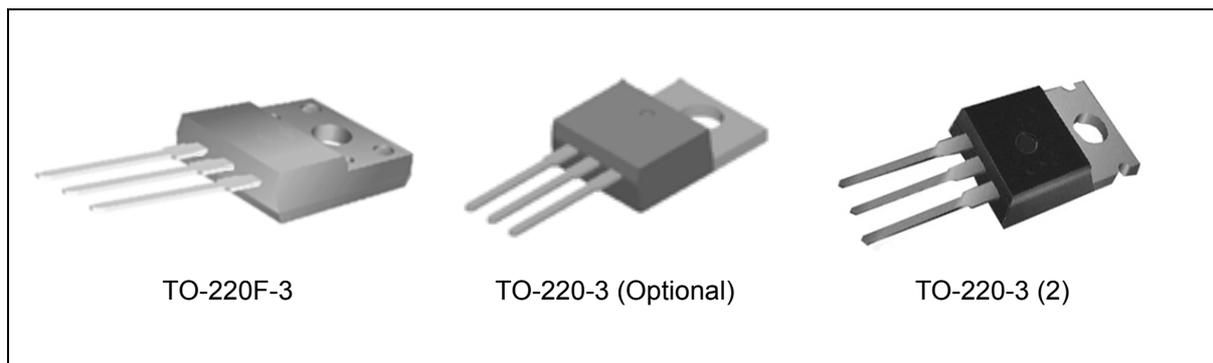


Figure 1. Package Types of MBR30H100C

Pin Configuration

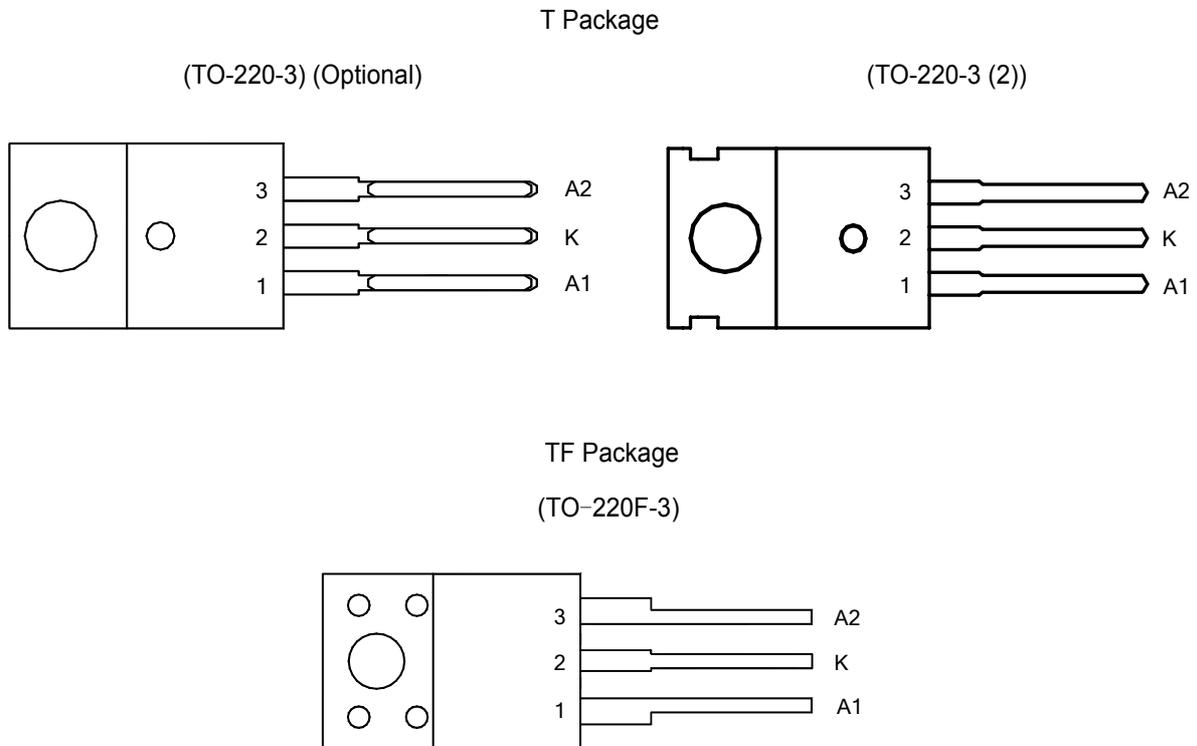


Figure 2. Pin Configuration of MBR30H100C (Front View)

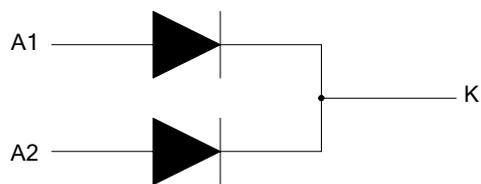


Figure 3. Internal Structure of MBR30H100C

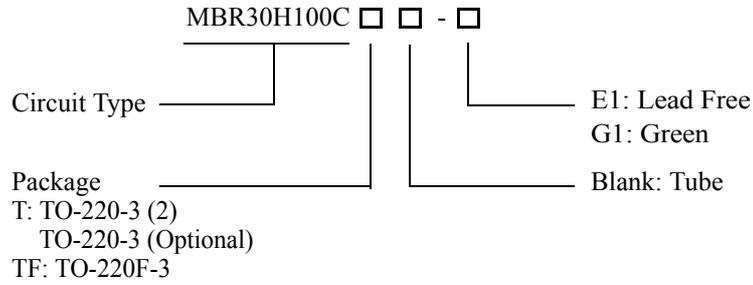


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Ordering Information



Package	Part Number		Marking ID		Packing Type
	Lead Free	Green	Lead Free	Green	
TO-220-3 (2)	MBR30H100CT-E1	MBR30H100CT-G1	MBR30H100CT-E1	MBR30H100CT-G1	Tube
TO-220F-3	MBR30H100CTF-E1	MBR30H100CTF-G1	MBR30H100CTF-E1	MBR30H100CTF-G1	Tube

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER **MBR30H100C**

Absolute Maximum Ratings (Each Diode Leg) (Note 1)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current (Rated V_R) $T_C=162^{\circ}C$	$I_{F(AV)}$	15	A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20kHz) $T_C=150^{\circ}C$	I_{FRM}	30	A
Non Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Half Wave, Single Phase, 60Hz)	I_{FSM}	250	A
Operating Junction Temperature (Note 2)	T_J	175	$^{\circ}C$
Storage Temperature Range	T_{STG}	-65 to 175	$^{\circ}C$
Voltage Rate of Change (Rated V_R)	dv/dt	10000	V/ μs
ESD (Machine Model=C)		>400	V
ESD (Human Body Model=3B)		>8000	V

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Note 2: The heat generated must be less than the thermal conductivity from Junction to Ambient: $dP_D/dT_J < 1/\theta_{JA}$.

Thermal Characteristics

Parameter	Symbol	Condition	Value	Unit	
Maximum Thermal Resistance	θ_{JC}	Junction to Case	TO-220-3/ TO-220-3 (2)	2.0	$^{\circ}C/W$
			TO-220F-3	2.5	
	θ_{JA}	Junction to Ambient	TO-220-3/ TO-220-3 (2)	60	



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Electrical Characteristics (Each Diode Leg)

Parameter	Symbol	Condition	Value	Unit
Maximum Instantaneous Forward Voltage Drop (Note 3)	V_F	$I_F=15A, T_C=25^{\circ}C$	0.80	V
		$I_F=15A, T_C=125^{\circ}C$	0.67	
		$I_F=30A, T_C=25^{\circ}C$	0.93	
		$I_F=30A, T_C=125^{\circ}C$	0.80	
Maximum Instantaneous Reverse Current (Note 3)	I_R	Rated DC Voltage, $T_C=125^{\circ}C$	6.0	mA
		Rated DC Voltage, $T_C=25^{\circ}C$	0.0045	

Note 3: Pulse Test: Pulse Width=300 μ s, Duty Cycle \leq 2.0%.



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Typical Performance Characteristics

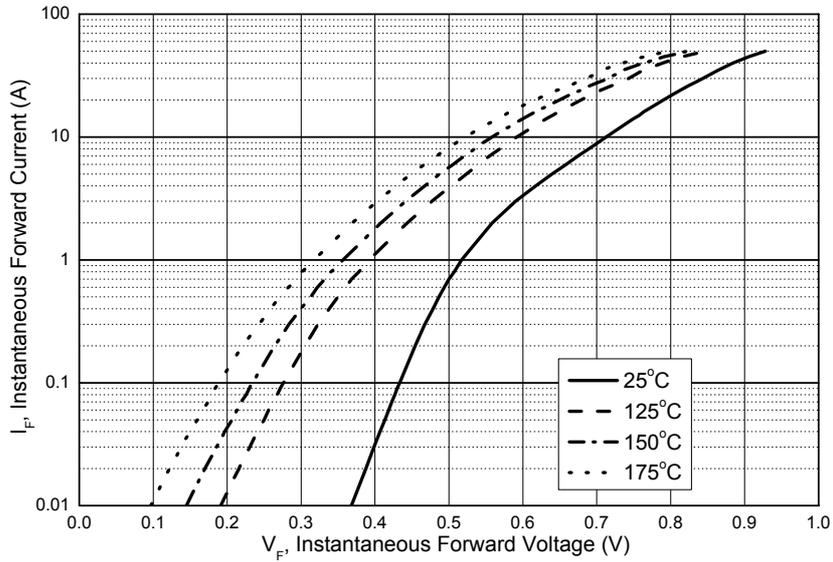


Figure 4. Typical Forward Voltage

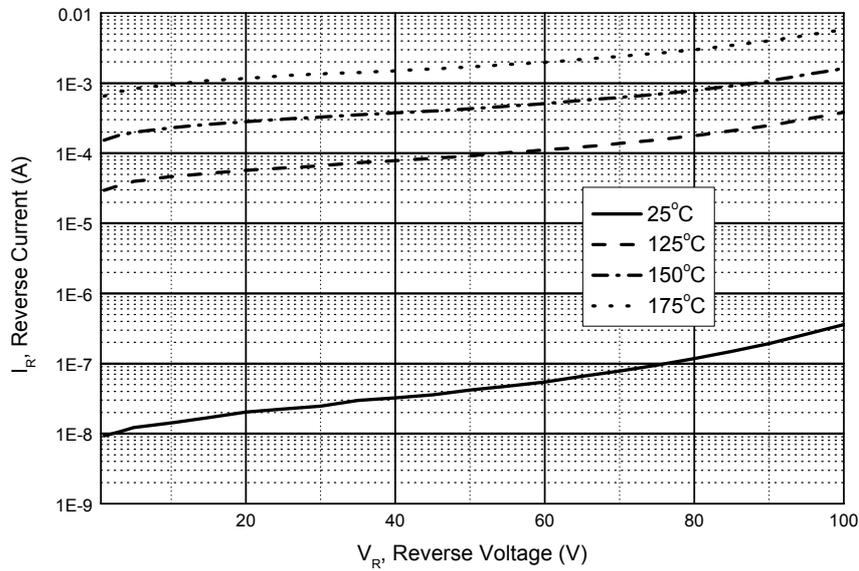


Figure 5. Typical Reverse Current

Typical Performance Characteristics (Continued)

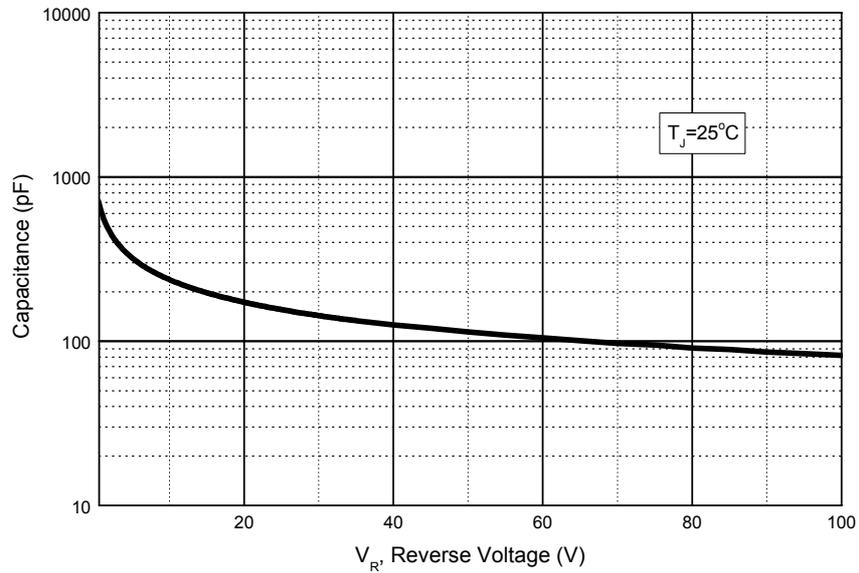


Figure 6. Capacitance vs. V_R , Reverse Voltage

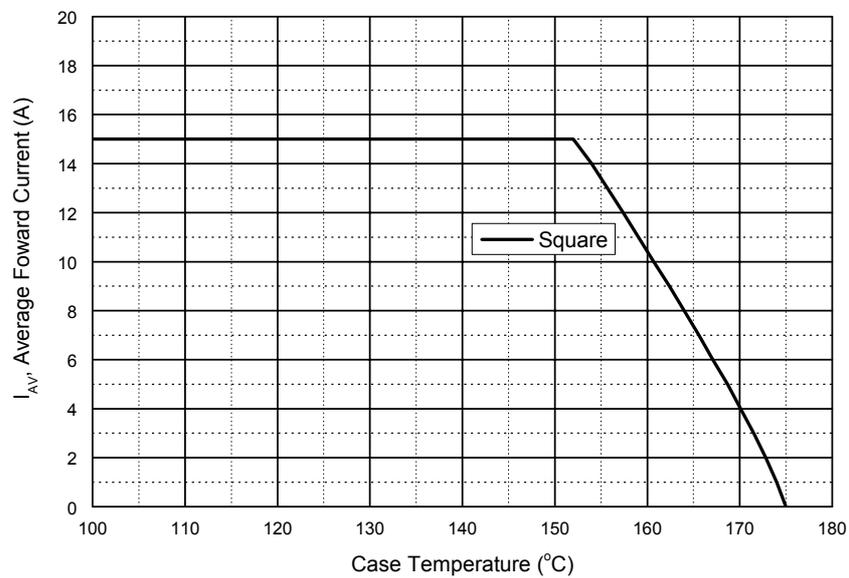


Figure 7. Average Forward Current vs. Case Temperature (Square, Each Diode)



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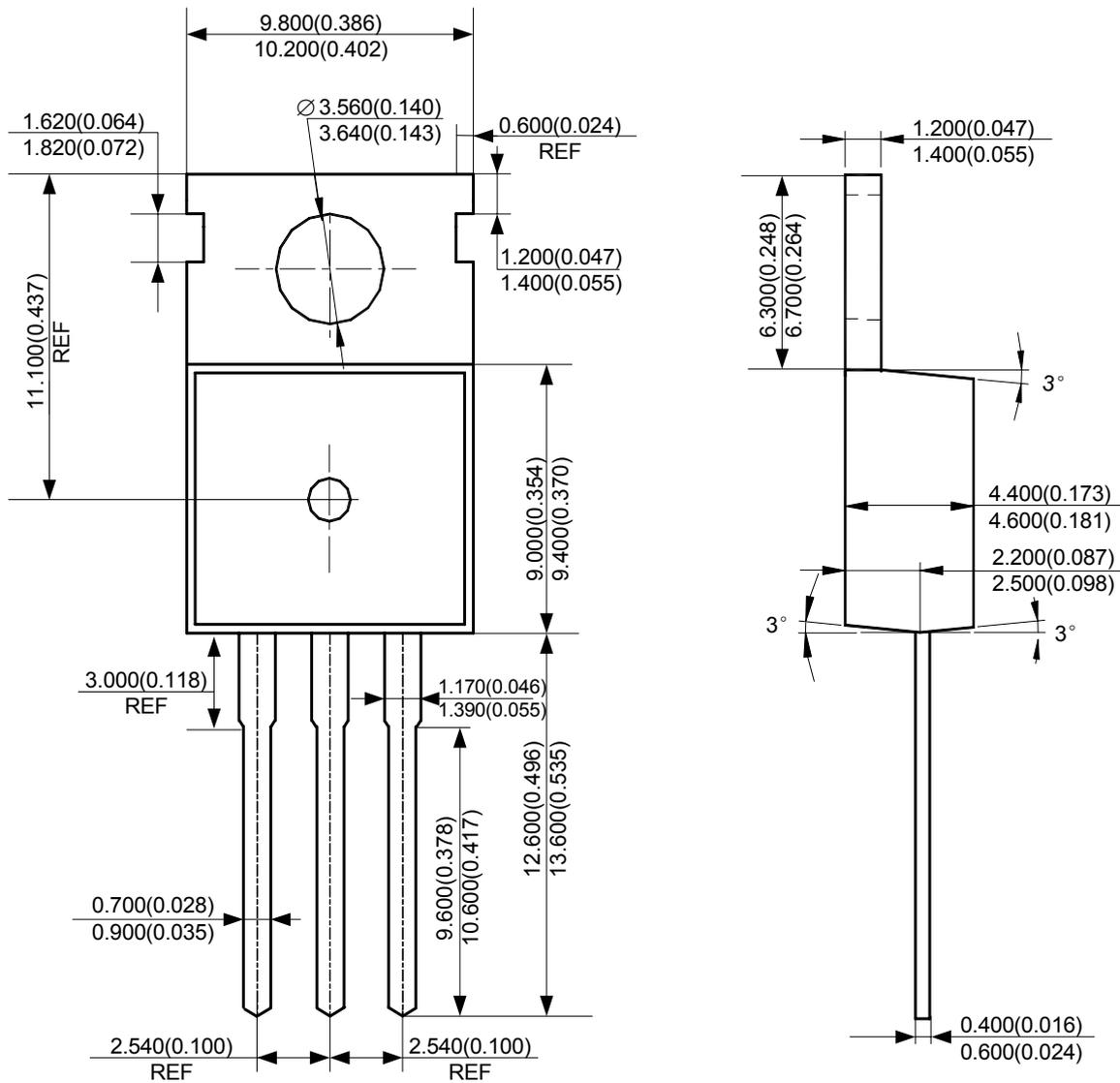
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Mechanical Dimensions (Continued)

TO-220-3 (2)

Unit: mm(inch)





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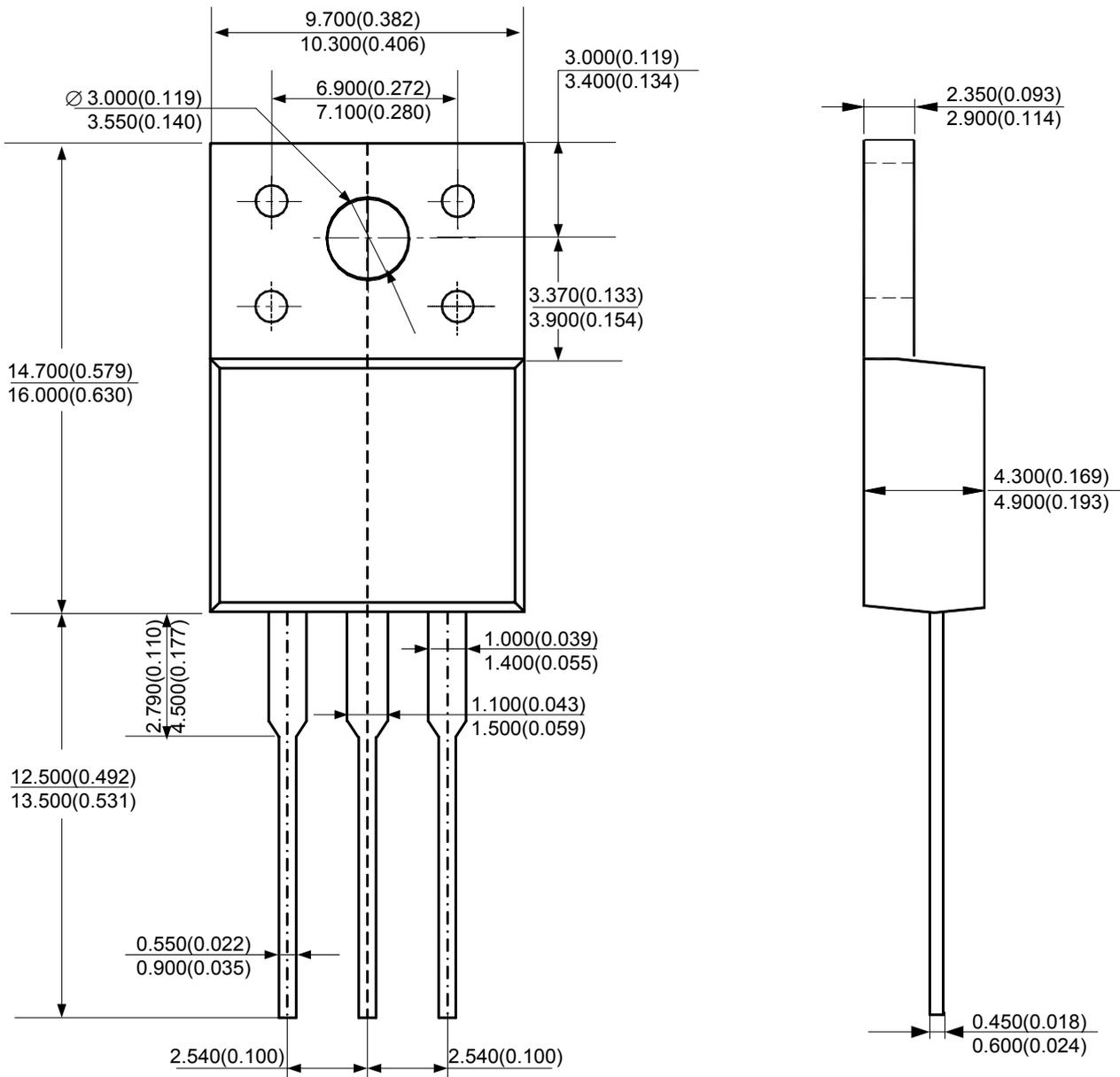
HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MBR30H100C

Mechanical Dimensions (Continued)

TO-220F-3

Unit: mm(inch)





Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
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Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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